

**SMALL SIGNAL COMPLEMENTARY PRE-BIASED DUAL TRANSISTOR**

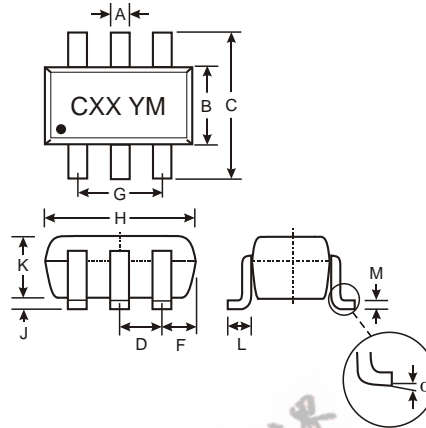
NEW PRODUCT

**Features**

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- **Lead Free/RoHS Compliant (Note 3)**
- Surface Mount Package Suited for Automated Assembly

**Mechanical Data**

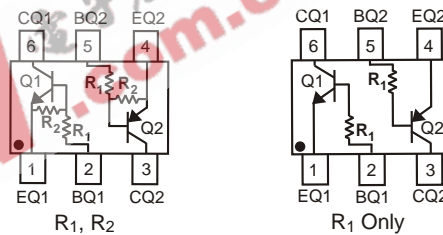
- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking: Date Code and Marking Code (See Page 4)
- Ordering Information (See Page 4)
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J		0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
	0°	8°

All Dimensions in mm

P/N	R1	R2	MARKING
DCX124EU	22K	22K	C17
DCX144EU	47K	47K	C20
DCX114YU	10K	47K	C14
DCX123JU	2.2K	47K	C06
DCX114EU	10K	10K	C13
DCX143TU	4.7K	-	C07
DCX143EU	4.7K	4.7K	C08
DCX114TU	10K	-	C12



Q1: NPN Transistor  
Q2: PNP Transistor

SCHMATIC DIAGRAM

**Maximum Ratings NPN Section @ T<sub>A</sub> = 25°C unless otherwise specified**

Characteristic	Symbol	Value	Unit
Supply Voltage, (6) to (1) and (4) to (3)	V <sub>CC</sub>	50	V
Input Voltage, (2) to (1) and (4) to (5)	V <sub>IN</sub>	-10 to +40 -10 to +40 -6 to +40 -5 to +12 -10 to +40 -5 V <sub>max</sub> -10 to +30 -5 V <sub>max</sub>	V
Output Current	I <sub>O</sub>	30 30 70 100 50 100 100 100	mA
Output Current	I <sub>C</sub> (Max)	100	mA
Power Dissipation (Total)	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R <sub>JA</sub>	625	°C/W
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Note: 1. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.  
2. 150mW per element must not be exceeded.  
3. No purposefully added lead.

**Maximum Ratings PNP Section** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage, (3) to (1)	V <sub>CC</sub>	50	V
Input Voltage, (2) to (1) DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143TU DCX143EU DCX114TU	V <sub>IN</sub>	+10 to -40 +10 to -40 +6 to -40 +5 to -12 +10 to -40 +5 V <sub>max</sub> +10 to -30 +5 V <sub>max</sub>	V
Output Current DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143TU DCX143EU DCX114TU	I <sub>O</sub>	-30 -30 -70 -100 -50 -100 -100 -100	mA
Output Current All	I <sub>C</sub> (Max)	-100	mA
Power Dissipation (Total) (Page 1: Note 2)	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient Air (Page 1: Note 1)	R <sub>JA</sub>	625	°C/W
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics NPN Section** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic (DCX143TU & DCX114TU only)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	50			V	I <sub>C</sub> = 50μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	50			V	I <sub>C</sub> = 1mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5			V	I <sub>E</sub> = 50μA
Collector Cutoff Current	I <sub>CB0</sub>			0.5	μA	V <sub>CB</sub> = 50V
Emitter Cutoff Current	I <sub>EBO</sub>			0.5	μA	V <sub>EB</sub> = 4V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			0.3	V	I <sub>C</sub> /I <sub>B</sub> = 2.5mA / 0.25mA DCX143TU I <sub>C</sub> /I <sub>B</sub> = 1mA / 0.1mA DCX114TU
DC Current Transfer Ratio	h <sub>FE</sub>	100	250	600		I <sub>C</sub> = 1mA, V <sub>CE</sub> = 5V
Input Resistor (R <sub>1</sub> ) Tolerance	R <sub>1</sub>	-30		+30	%	
Gain-Bandwidth Product	f <sub>T</sub>		250		MHz	V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz

**Electrical Characteristics NPN Section (Continued)** @  $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU	$V_{I(off)}$	0.5 0.5 0.3 0.5 0.5 0.5	1.1 1.1  1.1 1.16		V	$V_{CC} = 5V, I_O = 100\mu A$
	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU		$V_{I(on)}$		1.9 1.9  1.9 1.99		
Output Voltage	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU	$V_{O(on)}$			0.1	0.3	V
Input Current	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU	$I_I$			0.36 0.18 0.88 3.6 0.88 0.88	mA	$V_I = 5V$
Output Current		$I_{O(off)}$			0.5	$\mu A$	$V_{CC} = 50V, V_I = 0V$
DC Current Gain	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU	$G_I$	56 68 68 80 30 50				$V_O = 5V, I_O = 5mA$ $V_O = 5V, I_O = 5mA$ $V_O = 5V, I_O = 10mA$ $V_O = 5V, I_O = 10mA$ $V_O = 5V, I_O = 5mA$ $V_O = 5V, I_O = 10mA$
Input Resistor ( $R_1$ ) Tolerance		$R_1$	-30		+30	%	
Resistance Ratio Tolerance		$R_2/R_1$	-20		+20	%	
Gain-Bandwidth Product		$f_T$		250		MHz	$V_{CE} = 10V, I_E = 5mA, f = 100MHz$

**Electrical Characteristics PNP Section** @  $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic (DCX143TU & DCX114TU only)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-50			V	$I_C = -50\mu A$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	-50			V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5			V	$I_E = -50\mu A$
Collector Cutoff Current	$I_{CBO}$			-0.5	$\mu A$	$V_{CB} = -50V$
Emitter Cutoff Current	$I_{EBO}$			-0.5	$\mu A$	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	$I_C/I_B = 2.5mA / 0.25mA$ DCX143TU $I_C/I_B = 1mA / 0.1mA$ DCX114TU
DC Current Transfer Ratio	$h_{FE}$	100	250	600		$I_C = -1mA, V_{CE} = -5V$
Input Resistor ( $R_1$ ) Tolerance	$R_1$	-30		+30	%	
Gain-Bandwidth Product	$f_T$		250		MHz	$V_{CE} = -10V, I_E = 5mA, f = 100MHz$

**Electrical Characteristics PNP Section (Continued)** @ T<sub>A</sub> = 25°C unless otherwise specified

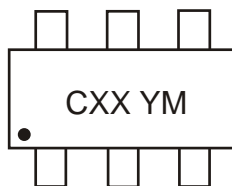
Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU	V <sub>I(off)</sub>	-0.5 -0.5 -0.3 -0.5 -0.5 -0.5	-1.1 -1.1		V	V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA
	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU	V <sub>I(on)</sub>		-1.9 -1.9 -1.1 -1.1 -1.9 -2.5	-3.0 -3.0 -1.4 -1.1 -3.0 -3.0		
Output Voltage	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU	V <sub>O(on)</sub>		-0.1	-0.3	V	I <sub>O</sub> /I <sub>I</sub> = -10mA / -0.5mA I <sub>O</sub> /I <sub>I</sub> = -10mA / -0.5mA I <sub>O</sub> /I <sub>I</sub> = -5mA / -0.25mA I <sub>O</sub> /I <sub>I</sub> = -5mA / -0.25mA I <sub>O</sub> /I <sub>I</sub> = -10mA / -0.5mA I <sub>O</sub> /I <sub>I</sub> = -10mA / -0.5mA
Input Current	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU	I <sub>I</sub>			-0.36 -0.18 -0.88 -3.6 -0.88 -0.88	mA	V <sub>I</sub> = -5V
Output Current		I <sub>O(off)</sub>			-0.5	μA	V <sub>CC</sub> = 50V, V <sub>I</sub> = 0V
DC Current Gain	DCX124EU DCX144EU DCX114YU DCX123JU DCX114EU DCX143EU	G <sub>I</sub>	56 68 68 80 30 40				V <sub>O</sub> = -5V, I <sub>O</sub> = -5mA V <sub>O</sub> = -5V, I <sub>O</sub> = -5mA V <sub>O</sub> = -5V, I <sub>O</sub> = -10mA V <sub>O</sub> = -5V, I <sub>O</sub> = -10mA V <sub>O</sub> = -5V, I <sub>O</sub> = -5mA V <sub>O</sub> = -5V, I <sub>O</sub> = -10mA
Input Resistor (R <sub>1</sub> ) Tolerance		R <sub>1</sub>	-30		+30	%	
Resistance Ratio Tolerance		R <sub>2</sub> /R <sub>1</sub>	-20		+20	%	
Gain-Bandwidth Product		f <sub>T</sub>		250		MHZ	V <sub>CE</sub> = -10V, I <sub>E</sub> = -5mA, f = 100MHZ

**Ordering Information** (Note 4)

Device	Packaging	Shipping
DCX124EU-7-F	SOT-363	3000/Tape & Reel
DCX144EU-7-F	SOT-363	3000/Tape & Reel
DCX114YU-7-F	SOT-363	3000/Tape & Reel
DCX123JU-7-F	SOT-363	3000/Tape & Reel
DCX114EU-7-F	SOT-363	3000/Tape & Reel
DCX143TU-7-F	SOT-363	3000/Tape & Reel
DCX143EU-7-F	SOT-363	3000/Tape & Reel
DCX114TU-7-F	SOT-363	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



CXX = Product Type Marking Code  
YM = Date Code Marking  
Y = Year ex: T = 2006  
M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

PNP SECTION

NEW PRODUCT

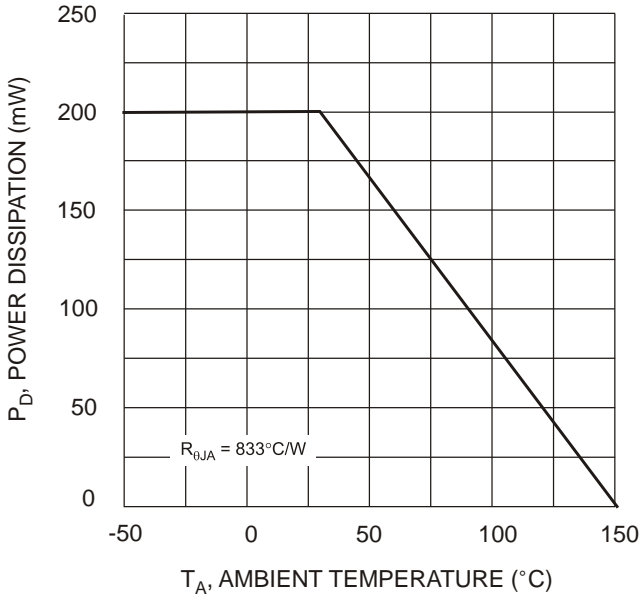


Fig. 1 Derating Curve

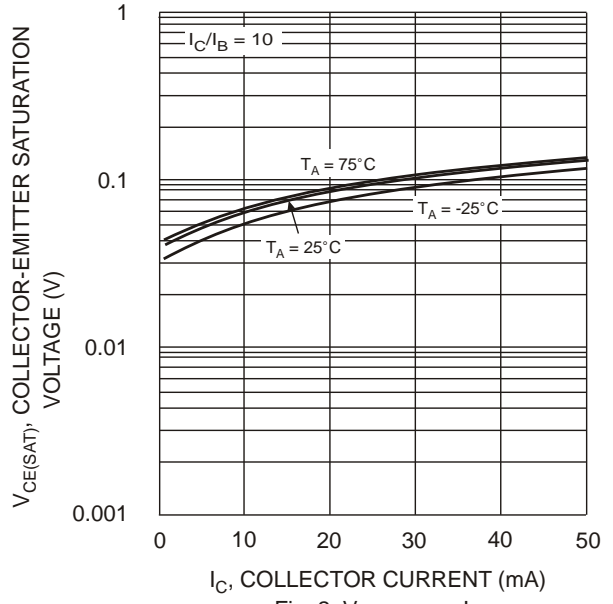


Fig. 2  $V_{CE(SAT)}$  vs.  $I_C$

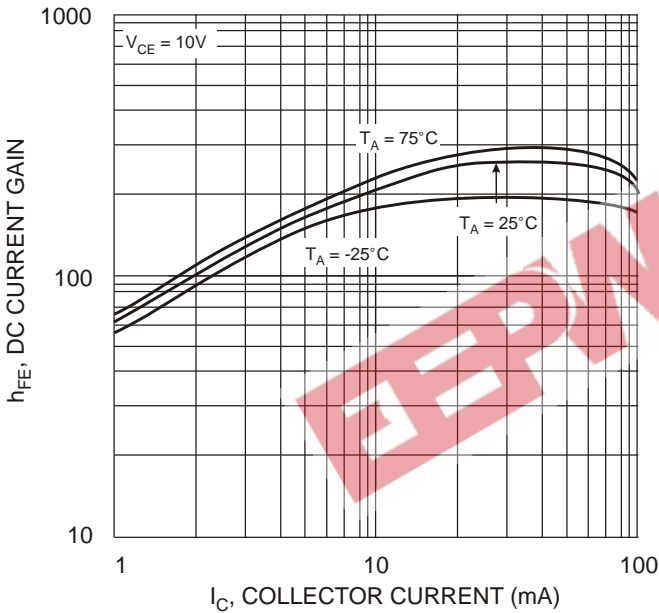


Fig. 3 DC Current Gain

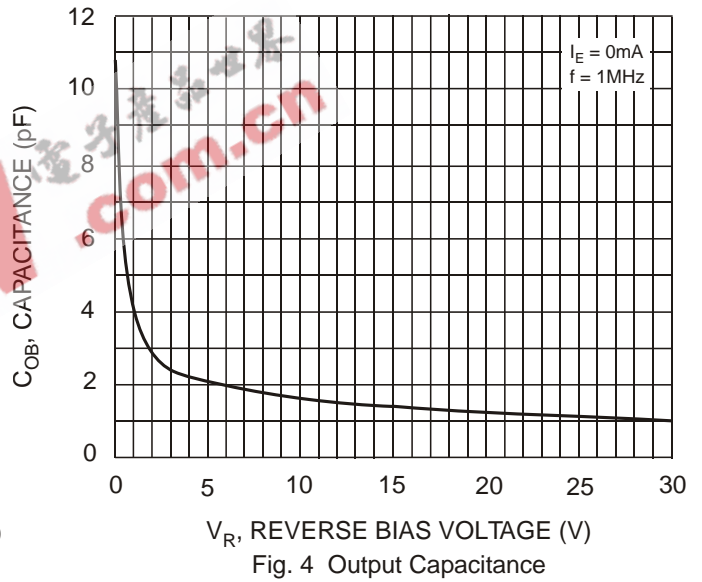


Fig. 4 Output Capacitance

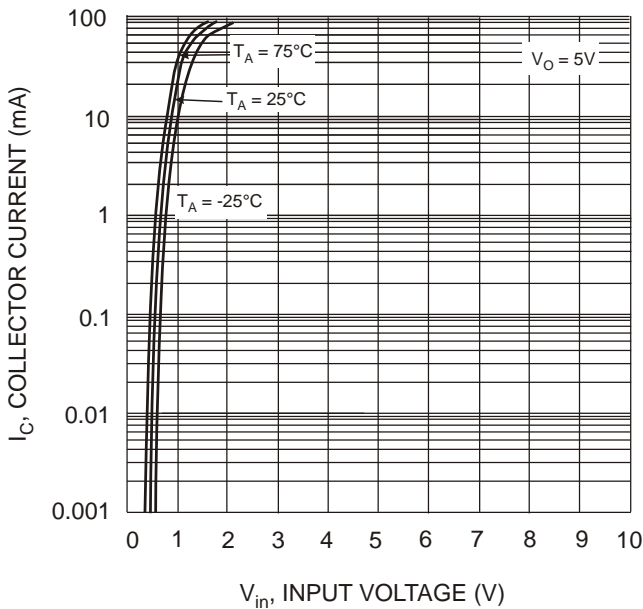


Fig. 5 Collector Current Vs. Input Voltage

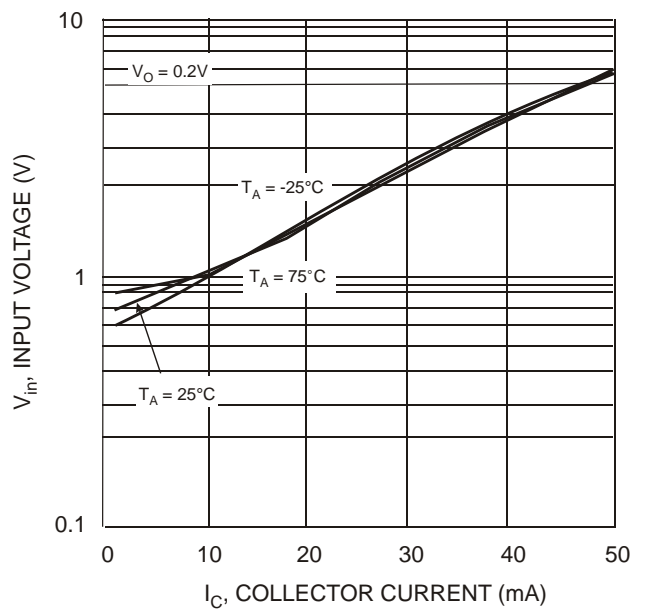


Fig. 6 Input Voltage vs. Collector Current

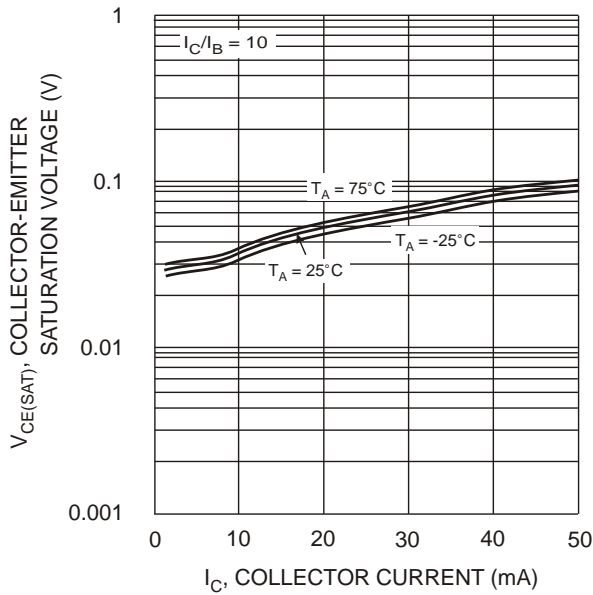


Fig. 7  $V_{CE(SAT)}$  vs.  $I_C$

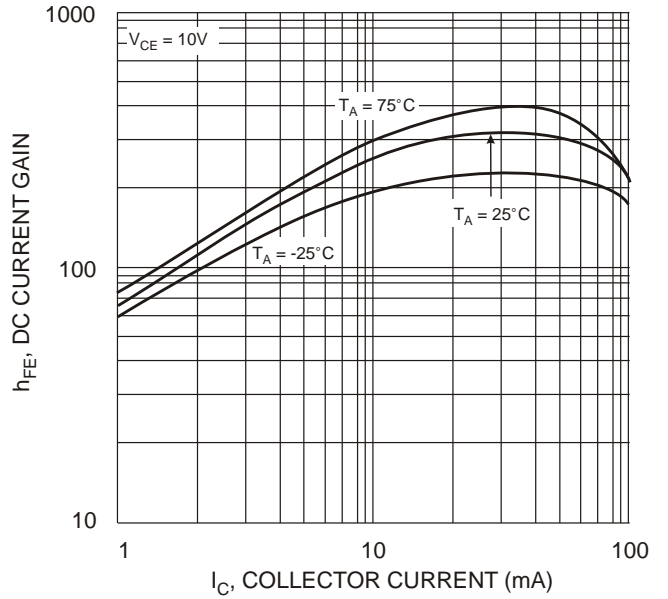


Fig. 8 DC Current Gain

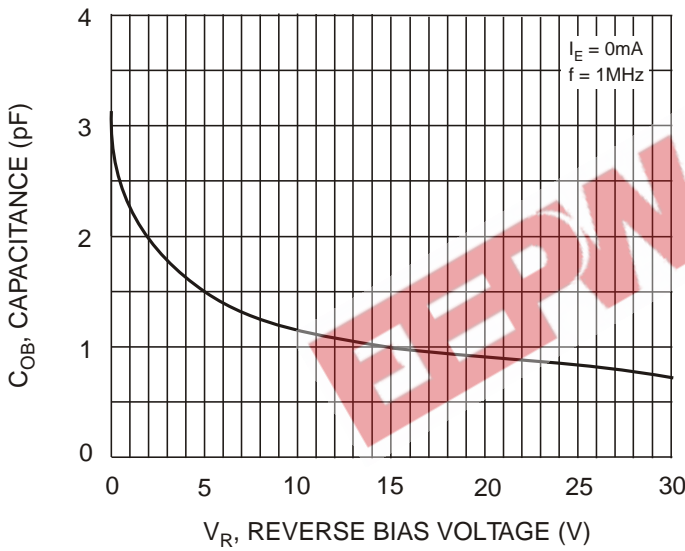


Fig. 9 Output Capacitance

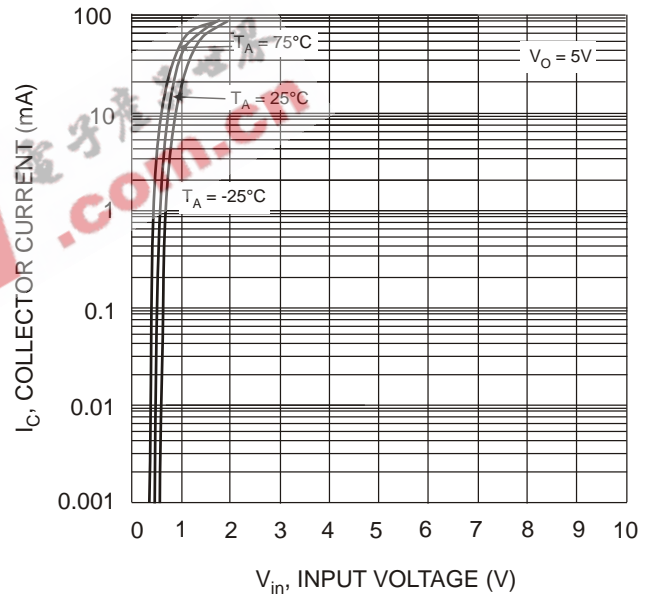


Fig. 10 Collector Current Vs. Input Voltage

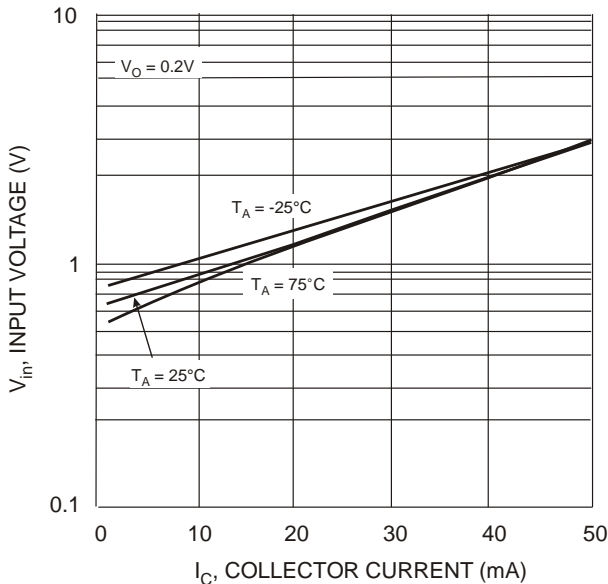


Fig. 11 Input Voltage vs. Collector Current

PNP SECTION

NEW PRODUCT

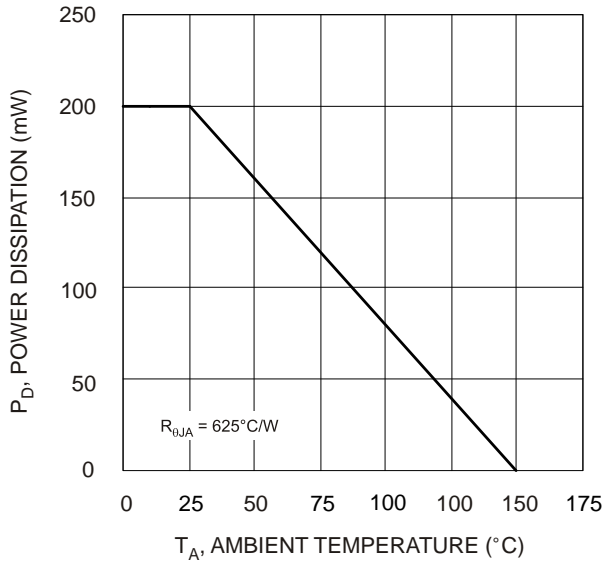


Fig. 12 Power Derating Curve

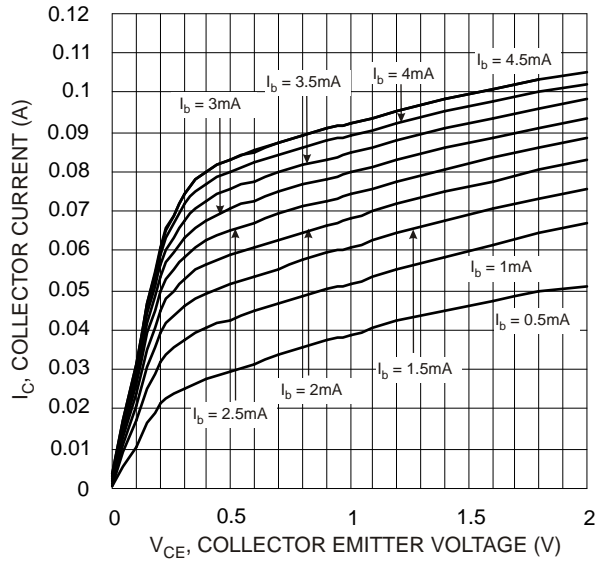


Fig. 13  $V_{CE}$  vs  $I_C$

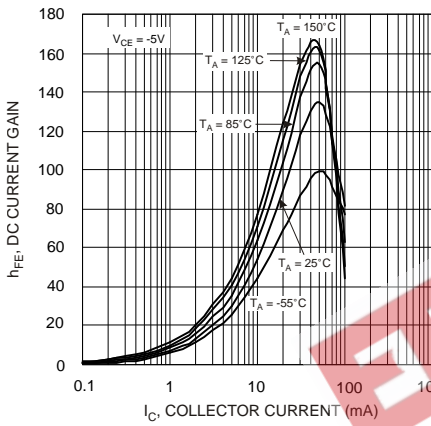


Fig. 14 DC Current Gain

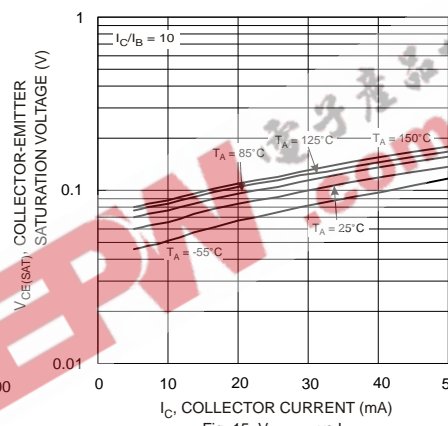


Fig. 15  $V_{CE(SAT)}$  vs  $I_C$

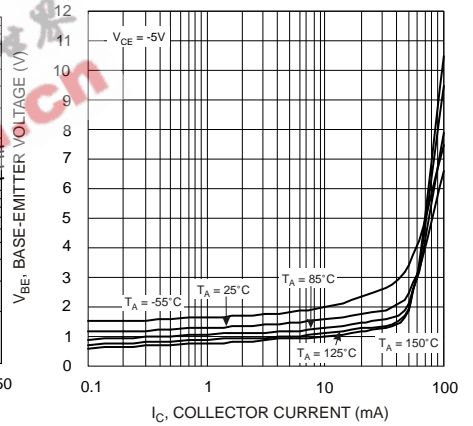


Fig. 16  $V_{BE}$  vs  $I_C$

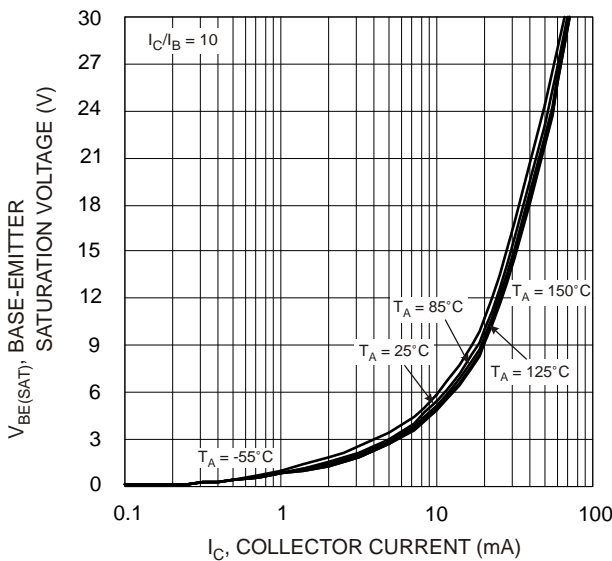


Fig. 17  $V_{BE(SAT)}$  vs  $I_C$

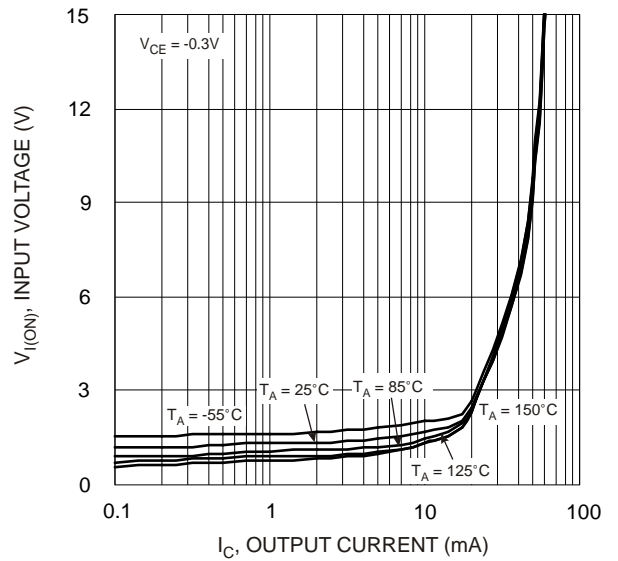


Fig. 18  $V_{I(ON)}$  vs  $I_C$



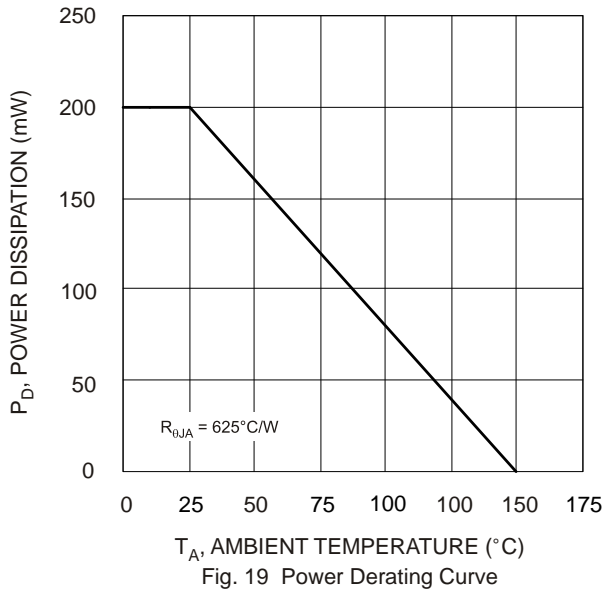


Fig. 19 Power Derating Curve

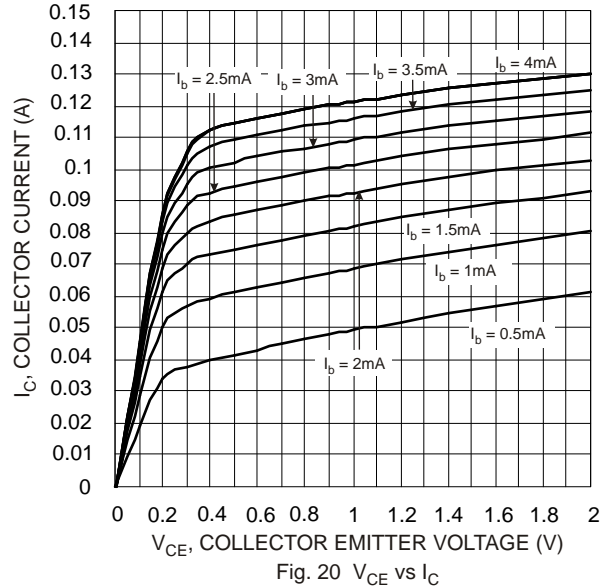


Fig. 20  $V_{CE}$  vs  $I_C$

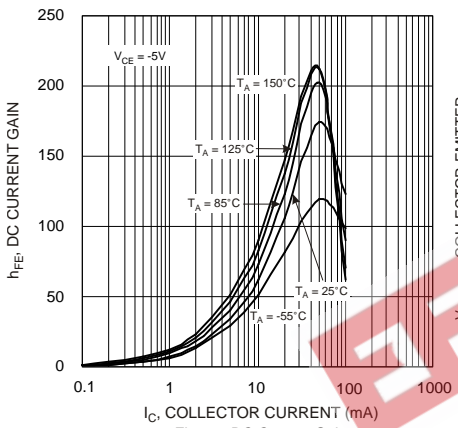


Fig. 21 DC Current Gain

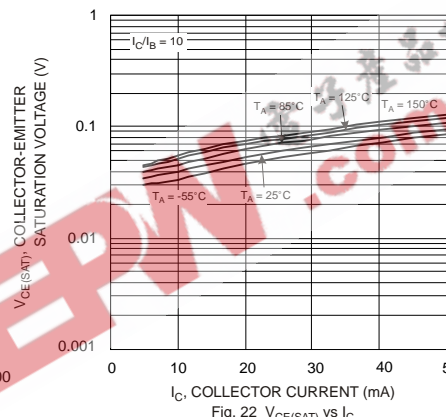


Fig. 22  $V_{CE(SAT)}$  vs  $I_C$

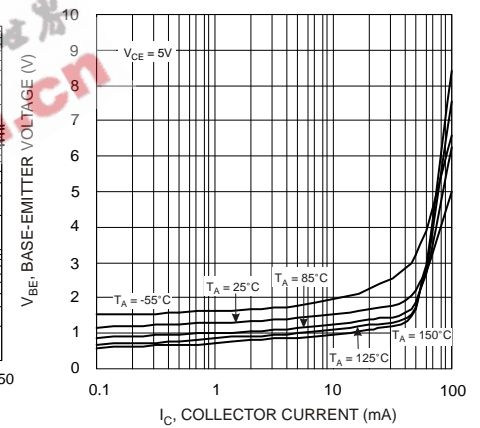


Fig. 23  $V_{BE}$  vs  $I_C$

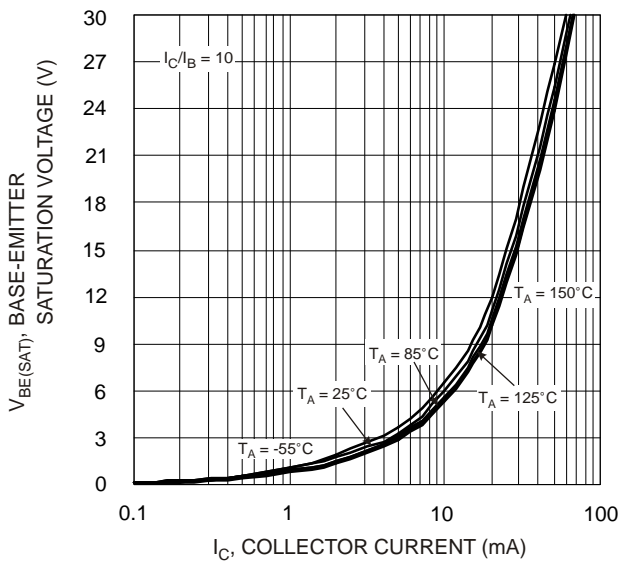


Fig. 24  $V_{BE(SAT)}$  vs  $I_C$

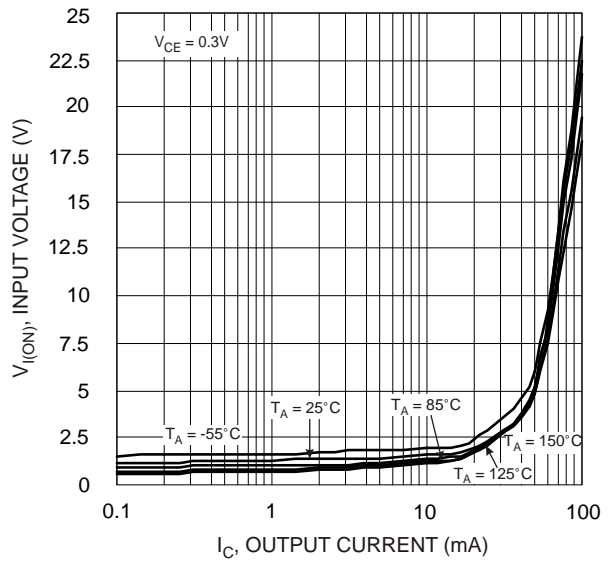


Fig. 25  $V_{(ON)}$  vs  $I_C$



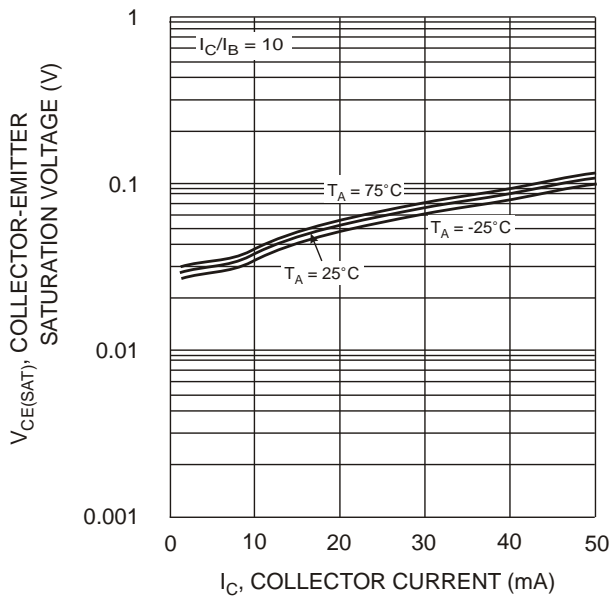


Fig. 26  $V_{CE(SAT)}$  vs.  $I_C$

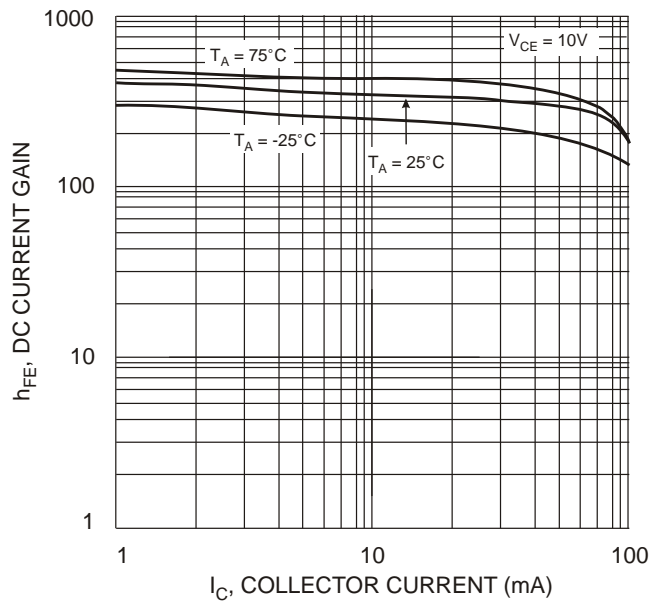


Fig. 27 DC Current Gain

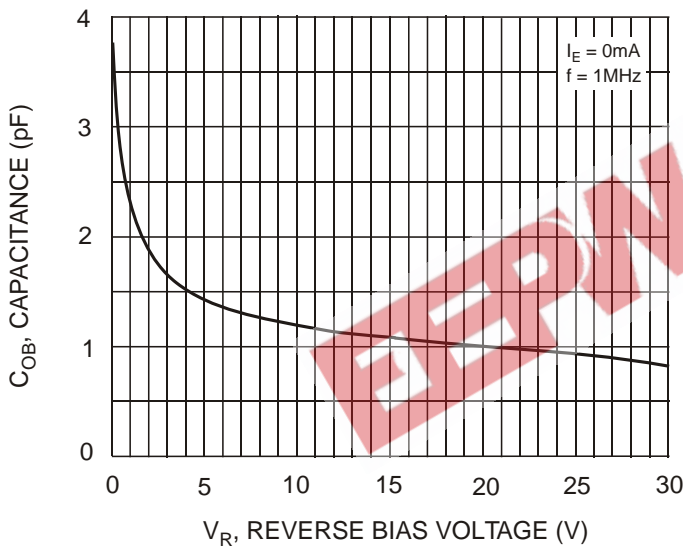


Fig. 28 Output Capacitance

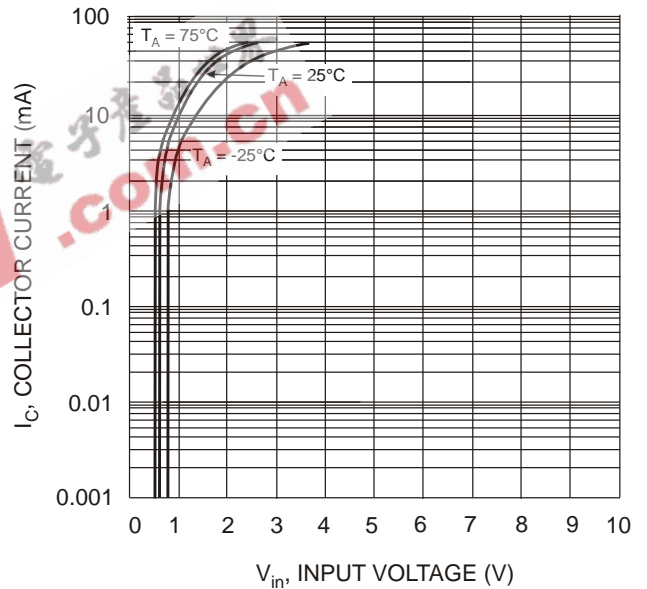


Fig. 29 Collector Current Vs. Input Voltage

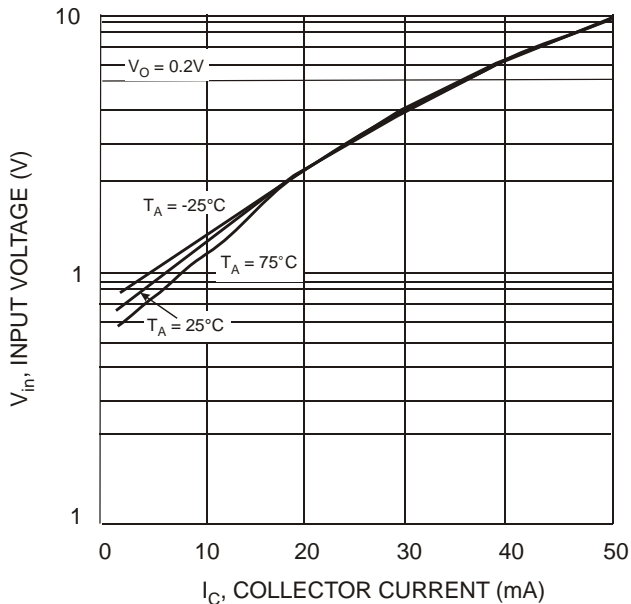


Fig. 30 Input Voltage vs. Collector Current

NPN SECTION

NEW PRODUCT

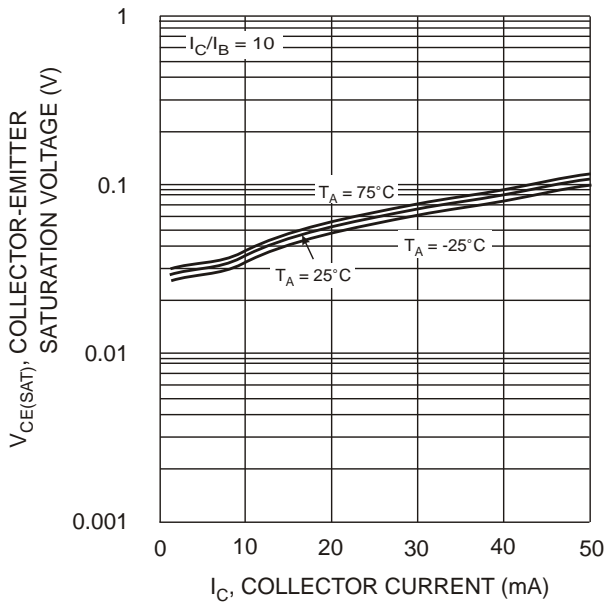


Fig. 31  $V_{CE(SAT)}$  vs.  $I_C$

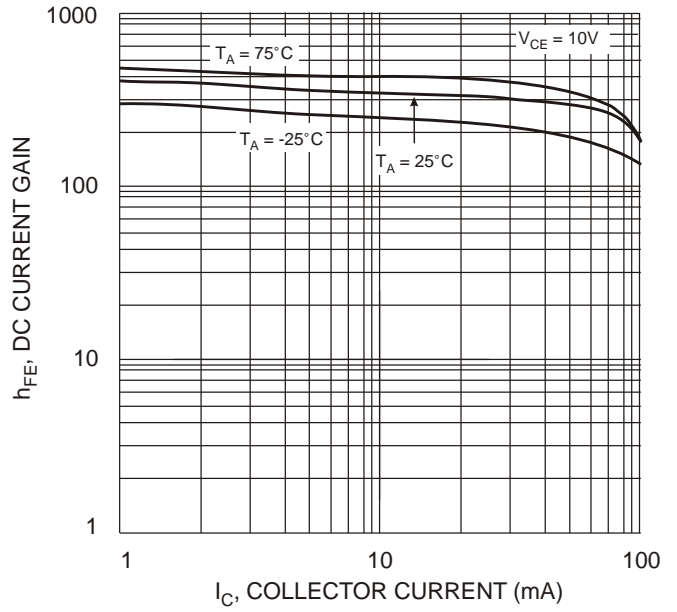


Fig. 32 DC Current Gain

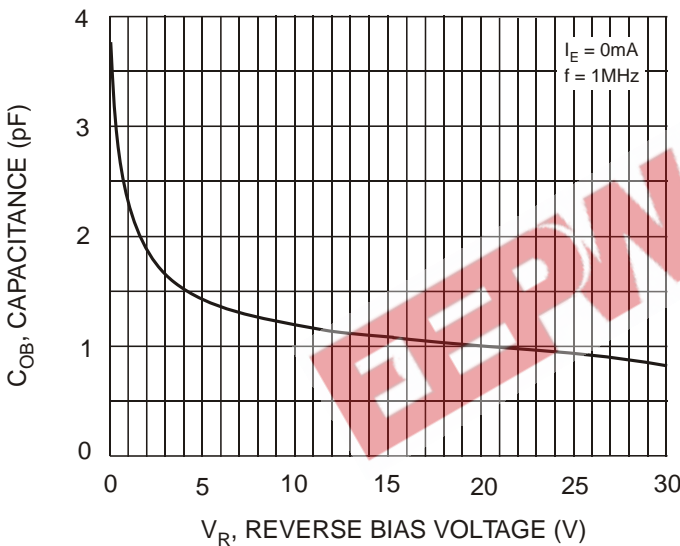


Fig. 33 Output Capacitance

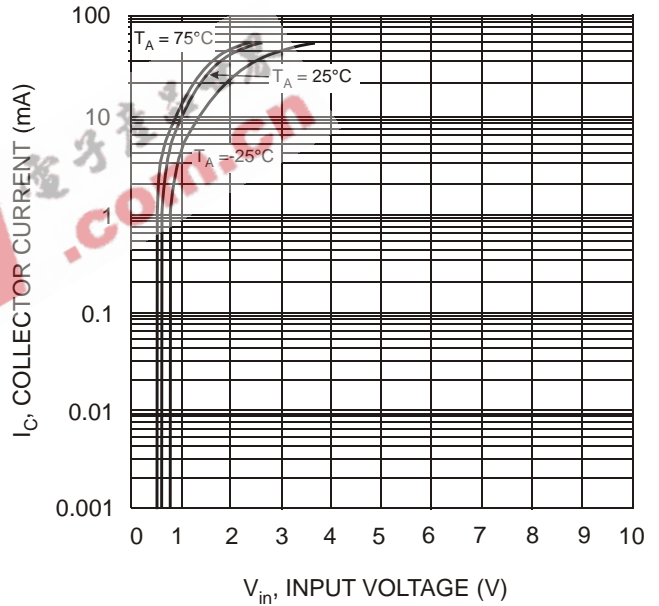


Fig. 34 Collector Current Vs. Input Voltage

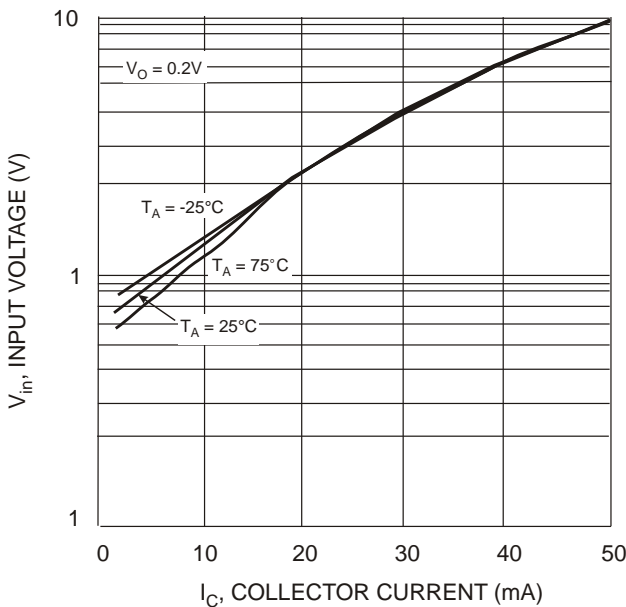


Fig. 35 Input Voltage vs. Collector Current

IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.

EEPW 电子產品世界  
.com.cn